

[TuB1] Lasers

Session Date	July 14 (Tue.), 2026
Session Time	08:30–10:15
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Dr. Andre Maaßdorf (Ferdinand–Braun–Institute, Germany) Dr. Nick Bailey (University of Sheffield, United Kingdom)

[TuB1–1] [Invited]

08:30–09:00

High Efficiency GaN–Based VCSELs with AlInN/GaN DBRs Grown by MOVPE

Tetsuya Takeuchi, Satoshi Kamiyama, and Motoaki Iwaya, Meijo University, Japan

[TuB1–2]

09:00–09:15

3.2–W InGaN–Based Photonic Crystal Surface Emitting Laser

Qian Sun, Chinese Academy of Sciences, China

[TuB1–3]

09:15–09:30

WITHDRAWN

[TuB1–4]

09:30–09:45

Extending the Concept of Quantum Mechanics to Bottom–Up Semiconductor Lasers

Wei Wen Wong, Xiaoying Huang, Jihua Zhang, Gaurang Garg, Olivier Lee Cheong Lem, Chennupati Jagadish, and Hoe Tan, The Australian National University, Australia

[TuB1–5]

09:45–10:00

A Novel Monolithic High–Contrast Grating VCSEL Grown by MOVPE for Near–Infrared Emission

Mikołaj Badura¹, Justyna Olejnik¹, Wojciech Dawidowski¹, Jan M. Śmigiel¹, Damian Radziejewicz¹, Adriana Łozińska¹, Marcin Gębski², Magdalena Marciniak², Tomasz Czyszanowski², Weronika Głowadzka³, Marek Ekielski³, Iwona Sankowska³, Anna Szerling³, and Beata Ściana¹, ¹Wrocław University of Science and Technology, Poland, ²Lodz University of Technology, Poland, ³Łukasiewicz Research Network, Poland

[TuB1-6]

10:00-10:15

Design and Development of InGaN-Based VECSEL Structures for High-Power Single-Mode Green Emission

Lucja Marona, Szymon Grzanka, Agata Bojarska, and Piotr Perlin, Institute of High-Pressure Physics PAS, Poland